

ABSTRACT OF THE DISCLOSURE

A semiconductor device having a semiconductor substrate; an insulating film formed on said semiconductor substrate; a ferroelectric capacitor having a lower electrode, a ferroelectric film and an upper electrode which are stacked sequentially on the insulating film; a first hydrogen barrier film; a first inter-layer insulating film covering said ferroelectric capacitor; and a second inter-layer insulating film stacked on the first inter-layer insulating film, the first hydrogen barrier film being interposed between the first and second interlayer insulating films is proposed.